MICROWAVE POWER GaN HEMT TGI5964-120L

MICROWAVE SEMICONDUCTOR TECHNICAL DATA

FEATURES

·BROAD BAND INTERNALLY MATCHED HEMT ·HIGH POWER

Pout= 51.0dBm at Pin= 43dBm

·HIGH GAIN

GL= 13.5dB at Pin= 20dBm

·LOW INTERMODULATION DISTORTION

IM3= -25dBc(Min.) at Pout= 44dBm (Single Carrier Level)

·HERMETICALLY SEALED PACKAGE



CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power	Pout	VDS= 24V IDSset= 4.0A f= 5.9 to 6.4GHz @Pin= 43dBm	dBm	50.0	51.0	_
Drain Current	IDS1		А		10.0	12.0
Power Added Efficiency	ηadd		%	_	44	_
Linear Gain	GL	@Pin= 20dBm	dB	12.5	13.5	
Gain flatness	ΔG		dB	_		±0.8
3rd Order Intermodulation Distortion	IM3	Two-Tone Test Po= 44dBm, ∆f= 5MHz (Single Carrier Level)	dBc	-25	-30	_
Drain Current	IDS2		А	_	_	8.0
Channel Temperature Rise	∆Tch	(VDS × IDS + Pin – Pout) × Rth(c-c)	°C		120	140

RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

Recommended Gate Resistance(Rg): 28 Ω

ELECTRICAL CHARACTERISTICS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 5V IDS= 10.0A	S	_	8.0	_
Pinch-off Voltage	VGSoff	VDS= 5V IDS= 46mA	V	-2.0	-4.0	-6.0
Saturated Drain Current	IDSS	VDS= 5V VGS= 0V	А	_	28	_
Gate-Source Breakdown Voltage	VGSO	IGS= -20mA	V	-10		
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W		0.6	0.8

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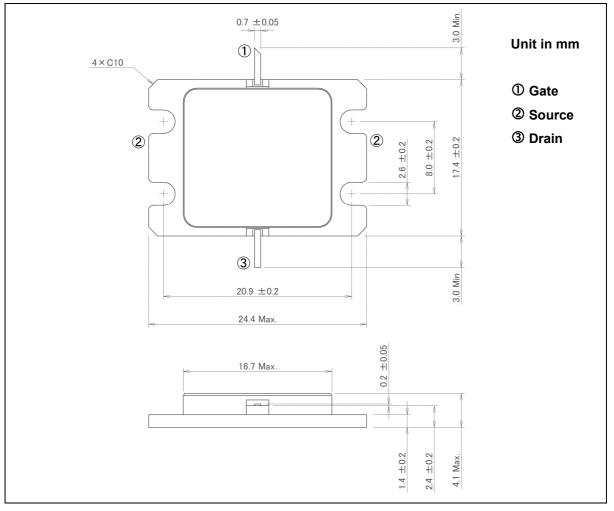
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ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

ROWAVE SEMICONDUCTOR TECHNICAL DATA

CHARACTERISTICS	SYMBOL	UNIT	RATING		
Drain-Source Voltage	VDS	V	50		
Gate-Source Voltage	VGS	V	-10		
Drain Current	IDS	А	18		
Total Power Dissipation (Tc= 25°C)	PT	W	280		
Channel Temperature	Tch	°C	250		
Storage Temperature	Tstg	°C	-65 to +175		

PACKAGE OUTLINE (7-AA06A)



HANDLING PRECAUTIONS FOR PACKAGE MODEL

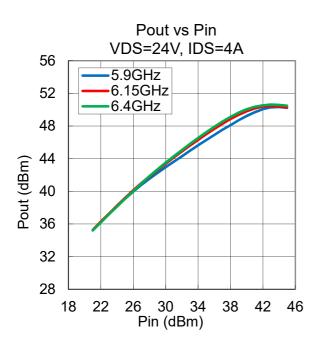
Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C or 3 seconds at 350°C.

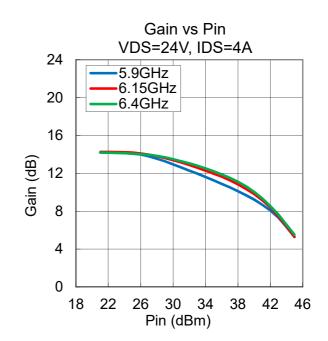
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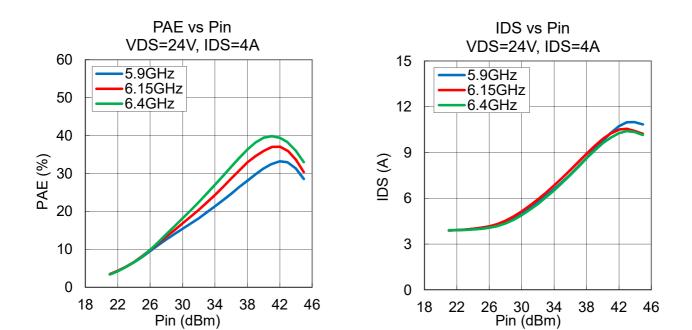
MICROWAVE SEMICONDUCTOR TECHNICAL DATA

·Pout , Gain , PAE , IDS vs. Pin

VDS= 24 V, IDSset= 4.0 A, f= 5.9, 6.15, 6.4 GHz, Ta= +25 °C





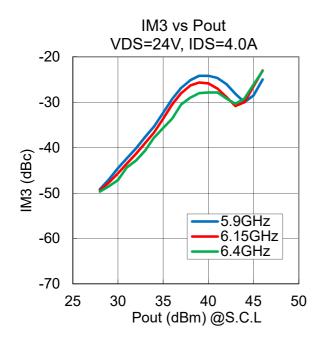


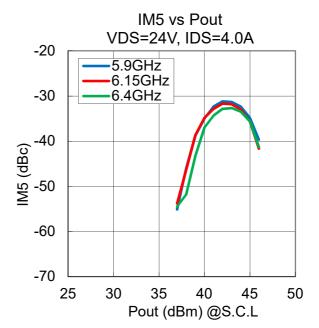
MICROWAVE POWER GaN HEMT TGI5964-120L

MICROWAVE SEMICONDUCTOR TECHNICAL DATA

·IM3, IM5 vs. Pout

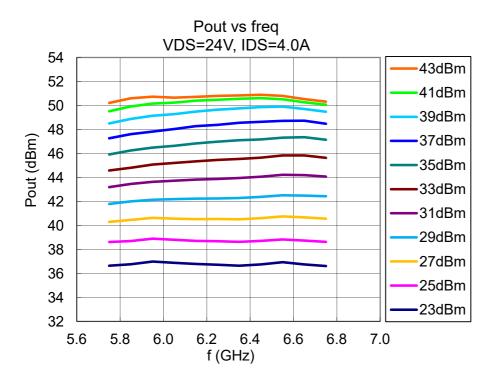
VDS= 24 V, IDSset= 4.0 A, f= 5.9, 6.15, 6.4 GHz, Δ f= 5 MHz , Ta= +25 $^{\circ}$ C





·Pout vs. Frequency

VDS= 24 V, IDSset= 4.0 A, Ta= +25 °C



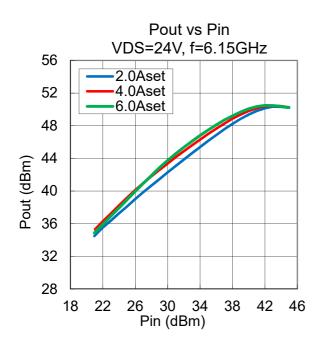
---- MICROWAVE SEMICONDUCTOR TECHNICAL DATA

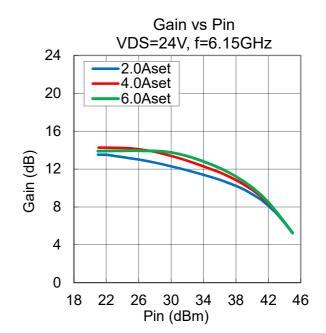
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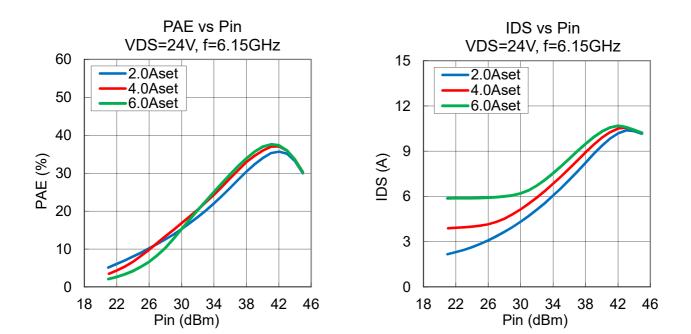
MICROWAVE SEMICONDUCTOR TECHNICAL DATA

·Pout, Gain, PAE, IDS vs. Pin vs. IDSset

VDS= 24 V, IDSset= 2.0, 4.0, 6.0 A, f= 6.15 GHz, Ta= +25 °C



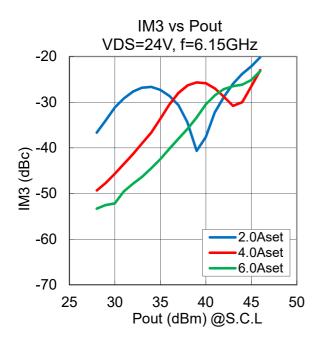


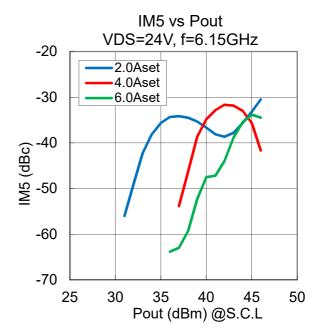


MICROWAVE SEMICONDUCTOR TECHNICAL DATA

·IM3, IM5 vs. Pout vs. IDSset

VDS= 24 V, IDSset= 2.0, 4.0, 6.0 A, f= 6.15 GHz, Δ f= 5 MHz, Ta= +25 °C

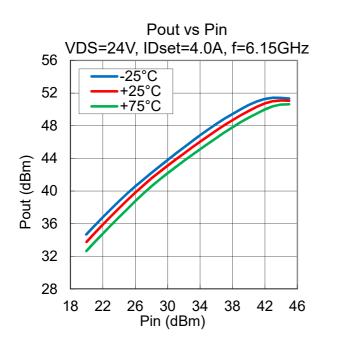


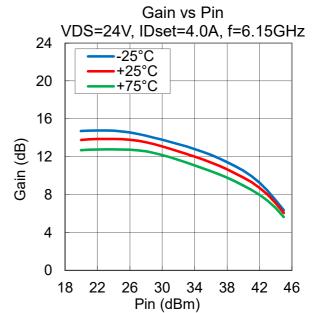


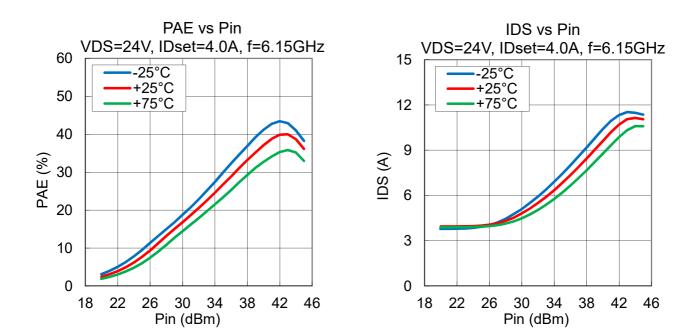
MICROWAVE SEMICONDUCTOR TECHNICAL DATA

·Pout, Gain, PAE, IDS vs. Pin vs. Temperature

VDS= 24 V, IDSset= 4.0 A, f= 6.15 GHz, Ta= -25, +25, +75 $\,^\circ \! \mathbb{C}$





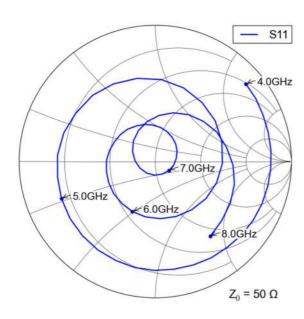


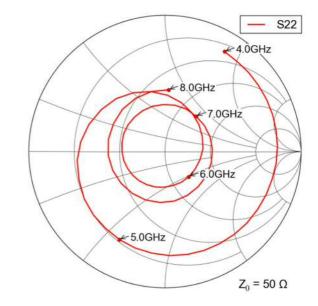
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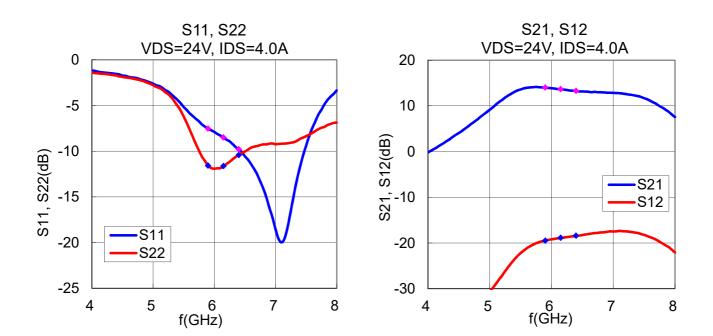
MICROWAVE SEMICONDUCTOR TECHNICAL DATA

·S-Parameters

VDS= 24 V, IDSset= 4.0 A, f= =4.0 to 8.0 GHz, Ta= +25 °C







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MICROWAVE SEMICONDUCTOR TECHNICAL DATA

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